

Silicon PNP Power Transistors

2N6132 2N6133 2N6134

DESCRIPTION

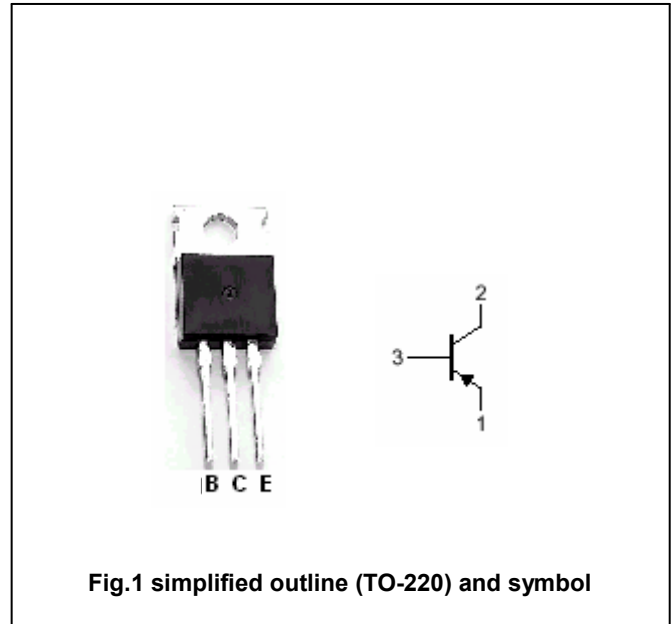
- With TO-220 package
- High power dissipation
- Complement to NPN type :
2N6129 2N6130 2N6131

APPLICATIONS

- Power amplifier and medium speed switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6132	-40	V
		2N6133	-60	
		2N6134	-80	
V _{CEO}	Collector-emitter voltage	2N6132	-40	V
		2N6133	-60	
		2N6134	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-7	A
I _B	Base current		-3	A
P _T	Total power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	2.5	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6132	I _C =-0.1A ; I _B =0			V
		2N6133				
		2N6134				
V _{CEsat}	Collector-emitter saturation voltage	2N6132	I _C =-7A; I _B =-1.2A			V
		2N6133				
		2N6134				
V _{BE}	Base-emitter on voltage	I _C =-2.5A ; V _{CE} =-4V			-1.4	V
I _{CEV}	Collector cut-off current	2N6132	V _{CE} =-40V; V _{BE} =1.5V T _C =150°C			mA
		2N6133				
		2N6134				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE}	DC current gain	I _C =-2.5A ; V _{CE} =-4V	20		100	
f _T	Transition frequency	I _C =-0.2A ; V _{CE} =-4V	2.5			MHz

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)